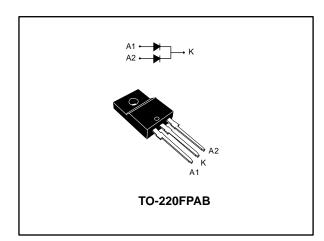


STPS30SM80C

Power Schottky rectifier

Datasheet - production data



Features

- High junction temperature capability
- Optimized trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified
- Insulated package TO-220FPAB
 - Insulated voltage: 2000 V_{RMS} sine

Description

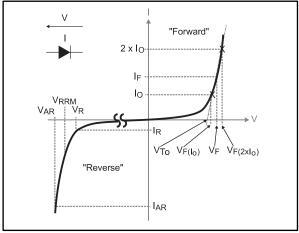
This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220FPAB, this device is particularly suited for use in notebook, game station, LCD TV and desktop adapters, providing these applications with a good efficiency at both low and high load.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	2 x 15 A
V _{RRM}	80 V
T _i (max.)	175 °C
V _F (typ.)	515 mV

Figure 1: Electrical characteristics





 V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in Figure 9. V_{AR} and I_{AR} are pulse measurements ($t_p < 1 \ \mu s$). V_R , I_R , V_{RRM} and V_F , are static characteristics.

Characteristics STPS30SM80C

1 Characteristics

Table 2: Absolute ratings (limiting values, per diode, at 25 °C, unless otherwise specified)

Symbol	Р	Value	Unit			
V _{RRM}	Repetitive peak reverse voltage			80	V	
I _{F(RMS)}	Forward rms current			30	Α	
I=	Average forward current	T _C = 105 °C	Per diode	15	Λ	
I _{F(AV)}	δ = 0.5, square wave	T _C = 70 °C	Per device	30	A	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal		220	Α	
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power	$t_p = 10 \ \mu s, T_j = 12$	545	W		
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage	t _p < 1 μs, T _j < 150 °C, I _{AR} < 22.8 A		100	V	
V _{ASM} ⁽²⁾	Maximum single pulse peak avalanche voltage	$t_p < 1 \ \mu s, \ T_j < 150$	100	V		
T _{stg}	Storage temperature range			-65 to +175	°C	
Tj	Maximum operating junction temperature (3)			175	°C	

Notes:

Table 3: Thermal parameters

Symbol	Parameter	Max. value	Unit		
D	Junction to case	Per diode	5.30	°C/W	
R _{th(j-c)}	Junction to case	Total	4.20	C/VV	
R _{th(c)}	Coupling		3.10	°C/W	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_{j \; (diode1)} = P_{(diode1)} \; x \; R_{th(j-c)} \; (per \; diode) \; + \; P_{(diode2)} \; x \; R_{th(c)}$$

⁽¹⁾For pulse time duration deratings, please refer to figure 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

⁽²⁾See Figure 9

 $^{^{(3)}(}dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

STPS30SM80C Characteristics

Table 4: Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Devene leskens sument	T _j = 25 °C	V V	-	10	40	μΑ
IR''	Reverse leakage current	T _j = 125 °C	$V_R = V_{RRM}$	-	7	20	mA
		T _j = 25 °C	I _F = 7.5 A	-	0.590	0.655	
	Forward voltage drop	T _j = 125 °C		-	0.515	0.555	
V _F ⁽²⁾		T _j = 25 °C	I _F = 15 A	-	0.715	0.790	.,
VF ⁽²⁾		T _j = 125 °C		-	0.600	0.675	V
		T _j = 25 °C	I _F = 30 A	-	0.860	0.965	
		T _j = 125 °C		-	0.710	0.830	

Notes:

 $^{(1)}$ Pulse test: t_p = 5 ms, δ < 2%

 $^{(2)} Pulse$ test: t_p = 380 $\mu s, \, \delta < 2\%$

To evaluate the conduction losses, use the following equation:

 $P = 0.520 \text{ x } I_{F(AV)} + 0.0103 \text{ x } I_{F^2(RMS)}$

Characteristics STPS30SM80C

1.1 Characteristics (curves)

Characteristics (curves)

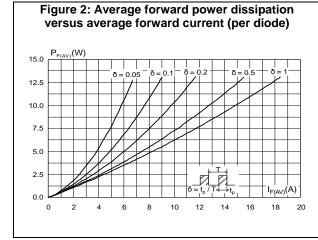


Figure 3: Average forward current versus ambient temperature (δ = 0.5, per diode)

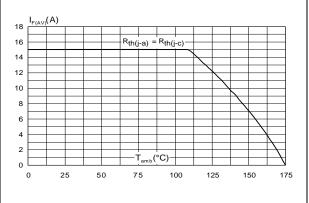


Figure 4: Normalized avalanche power derating versus pulse duration (T_j = 125 °C)

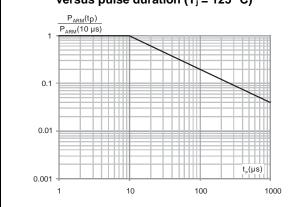


Figure 5: Relative thermal impedance junction to case versus pulse duration

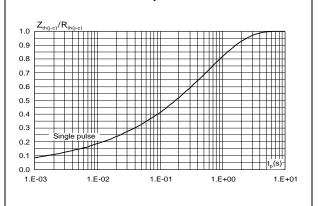


Figure 6: Reverse leakage current versus reverse voltage applied (typical values, per diode)

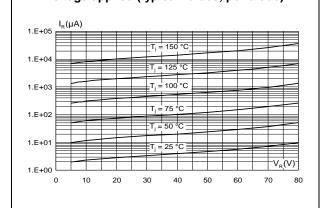
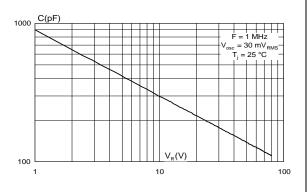


Figure 7: Junction capacitance versus reverse voltage applied (typical values, per diode)



STPS30SM80C Characteristics

current (per diode)

I_F(A)

T_j = 125 °C
(Maximum values)

T_j = 25 °C
(Maximum values)

T_j = 25 °C
(Maximum values)

Figure 8: Forward voltage drop versus forward

Figure 9: Reverse safe operating area $(t_p < 1 \ \mu s \ and \ T_j < 150 \ ^{\circ}C)$

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Package information STPS30SM80C

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

• Cooling method: by conduction (C)

• Epoxy meets UL 94,V0

Recommended torque value: 0.55 N⋅m

• Maximum torque value: 0.7 N·m

2.1 TO-220FPAB package information

H H L2 L3 L4 L5 Dia L7 L5 D L7

Figure 10: TO-220FPAB package outline

Table 5: TO-220FPAB package mechanical data

	Dimensions				
Ref.	Millin	neters	ers Inch		
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
В	2.5	2.7	0.098	0.106	
D	2.50	2.75	0.098	0.108	
Е	0.45	0.70	0.018	0.027	
F	0.75	1.0	0.03	0.039	
F1	1.15	1.70	0.045	0.067	
F2	1.15	1.70	0.045	0.067	
G	4.95	5.20	0.195	0.205	
G1	2.40	2.70	0.094	0.106	
Н	10.00	10.40	0.393	0.409	
L2	16.00	0 typ.	0.63	typ.	
L3	28.60	30.60	1.126	1.205	
L4	9.80	10.6	0.386	0.417	
L5	2.90	3.60	0.114	0.142	
L6	15.90	16.40	0.626	0.646	
L7	9.00	9.30	0.354	0.366	
Dia	3.0	3.20	0.118	0.126	

Ordering information STPS30SM80C

3 Ordering information

Table 6: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS30SM80CFP	PS30SM80CFP	TO-220FPAB	2.0 g	50	Tube

4 Revision history

Table 7: Document revision history

Date	Revision	Changes
11-Apr-2011	1	First issue.
12-May-2017	2	Removed D ² PAK, I ² PAK and TO-220AB packages.

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